

SOT-23 TRANSISTORS (continued)

Darlingtons

The following table is a listing of small-signal devices that have very high h_{FE} and input impedance characteristics. These devices utilize monolithic, cascade transistor construction.

Pinout: 1-Base, 2-Emitter, 3-Collector

Devices are listed in order of descending h_{FE} .

Device	Marking	$V_{(BR)CES}$	$V_{CE(sat)}$ Volts Max	$h_{FE} @ I_C$		
				Min	Max	mA
NPN						
MMBTA14LT1	1N	30	1.5	20K	—	100
MMBTA13LT1	1M	30	1.5	10K	—	100
PNP						
MMBTA64LT1	2V	30	1.5	20K	—	100

Low-Noise Transistors

The following table is a listing of small-signal devices intended for low noise applications in the audio range. These devices exhibit good linearity and are candidates for hi-fi and instrumentation equipment.

Pinout: 1-Base, 2-Emitter, 3-Collector

Devices are listed in order of ascending NF.

Device	Marking	NF dB Typ	$V_{(BR)CEO}$	$h_{FE} @ I_C$			f_T MHz Min
				Min	Max	mA	
NPN							
MMBT5089LT1	1R	2.0 ⁽¹⁾	25	400	—	10	50
MMBT2484LT1	1U	3.0 ⁽¹⁾	60	—	800	10	—
MMBT6428LT1	1KM	3.0	50	250	—	10	100
MMBT6429LT1	1L	3.0	45	500	—	10	100
PNP							
MMBT5087LT1	2Q	2.0 ⁽¹⁾	50	250	—	10	40

⁽¹⁾Max

High-Voltage Transistors

The following table is a listing of small-signal high-voltage devices designed for direct line operation requiring high voltage breakdown and relatively low current capability.

Pinout: 1-Base, 2-Emitter, 3-Collector

Devices are listed in order of descending breakdown voltage.

Device	Marking	$V_{(BR)CEO}$	$h_{FE} @ I_C$			f_T MHz Min
			Min	Max	mA	
NPN						
MMBT6517LT1	1Z	350	15	—	100	40
MMBTA42LT1	1D	300	40	—	30	50
MMBT5551LT1	G1	160	30	—	50	100
PNP						
MMBT6520LT1	2Z	350	15	—	100	40
MMBTA92LT1	2D	300	25	—	30	50
MMBT5401LT1	2L	150	50	—	50	100

See Packaging Information under Technical Data Section for reel size, quantity and ordering information.

Devices listed in bold, italic are Motorola preferred devices.